

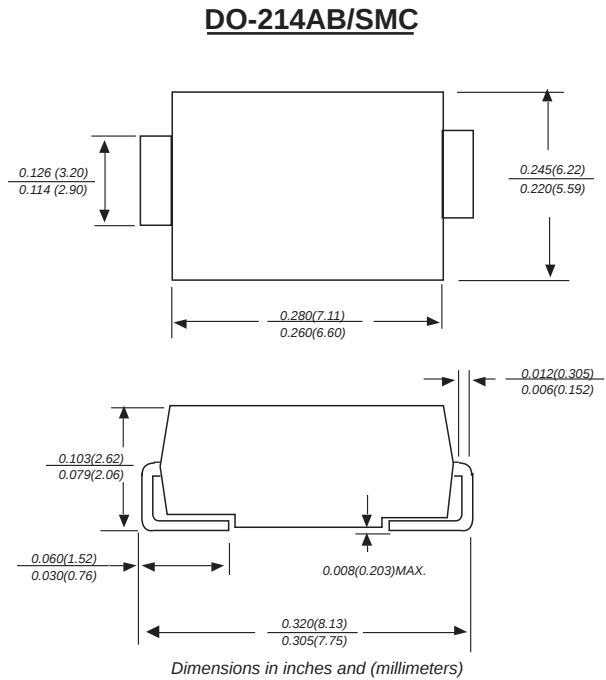
Surface Mount Fast Recovery Rectifier Diodes

Features

- Glass Passivated Die Construction
- Fast Recovery Time for High Efficiency
Low Forward Voltage Drop and High Current Capability
- Ideally Suited for Automatic Assembly
- Plastic Material: UL Flammability
- Classification Rating 94V-0

Mechanical Data

- Case: SMC/DO-214AB, Molded Plastic
- Terminals: Solder Plated, Solderable per MIL-STD-750, Method 2026
- Polarity: Cathode Band or Cathode Notch
- Marking: Type Number
- Weight: 0.21 grams (approx.)



Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise specified

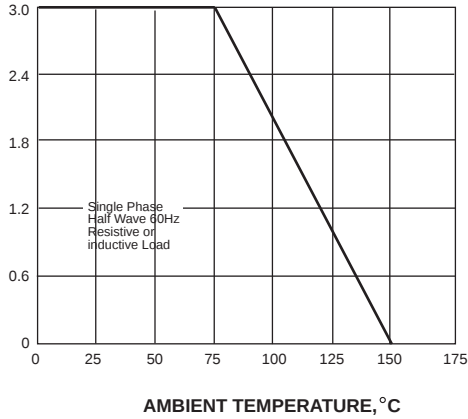
Characteristic	Symbol	RS3AC	RS3BC	RS3DC	RS3GC	RS3JC	RS3KC	RS3MC	Unit
Maximum repetitive peak reverse voltage	V _{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS voltage	V _{RMS}	35	70	140	280	420	560	700	V
Maximum DC blocking voltage	V _{DC}	50	100	200	400	600	800	1000	V
Maximum average forward rectified current at T _L =75°C	I _(AV)	3.0							A
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}	100.0							A
Maximum instantaneous forward voltage at 3.0A	V _F	1.3							V
Maximum DC reverse current T _A =25°C at rated DC blocking voltage T _A =100°C	I _R	5.0 100.0							μA
Maximum reverse recovery time (NOTE 1)	t _{rr}	150				250	500		ns
Typical junction capacitance (NOTE 2)	C _J	60.0							pF
Typical thermal resistance (NOTE 3)	R _{θJA}	50.0							°C/W
Operating junction and storage temperature range	T _J , T _{STG}	-50 to +150							°C

Note: 1. Reverse recovery condition $I_F = 0.5\text{A}$, $I_R = 1.0\text{A}$, $I_{rr} = 0.25\text{A}$
 2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.
 3. P.C.B. mounted with 0.2x0.2" (5.0x5.0mm) copper pad areas

Characteristic Curves $T_A = 25^\circ\text{C}$ unless otherwise noted

AVERAGE FORWARD RECTIFIED CURRENT,
AMPERES

FIG. 1- FORWARD CURRENT DERATING CURVE



PEAK FORWARD SURGE CURRENT,
AMPERES

FIG. 2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

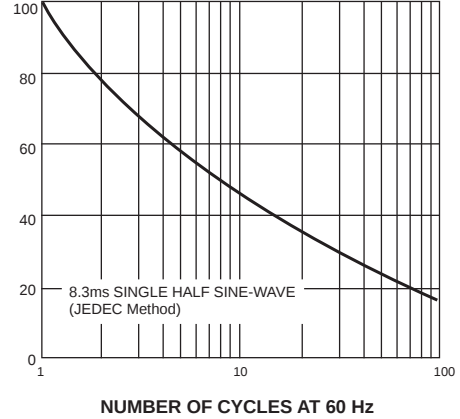


FIG. 3-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

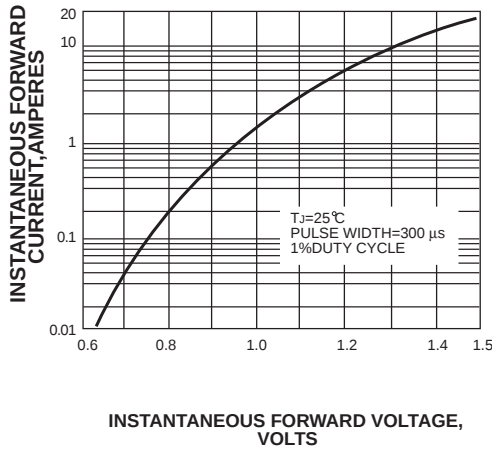


FIG. 4-TYPICAL REVERSE CHARACTERISTICS

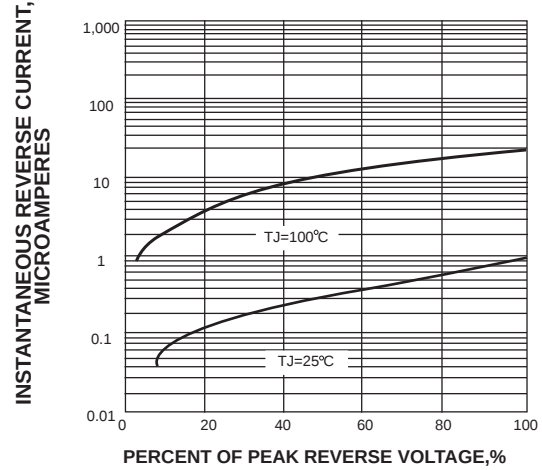


FIG. 5-TYPICAL JUNCTION CAPACITANCE

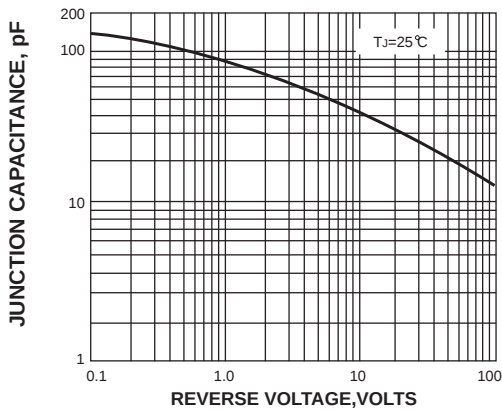
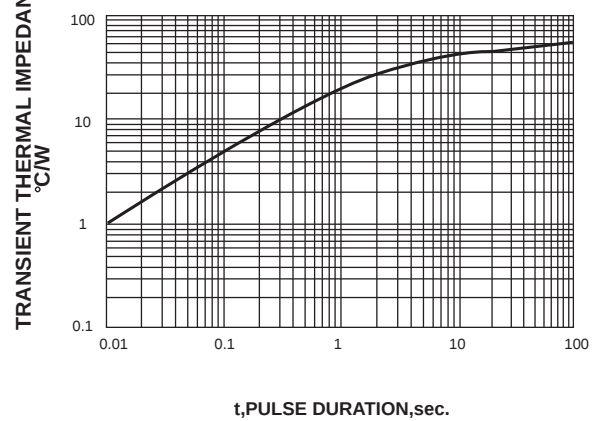


FIG. 6-TYPICAL TRANSIENT THERMAL IMPEDANCE



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